

ALTERNATIVE TO PTO/SB/08A/B  
(Based on PTO 08-08 version)

Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	10/537,804
				Filing Date	June 7, 2005
				First Named Inventor	Robert DWILINSKI
				Art Unit	1792
Examiner Name	F. C. Hiteshew				
Sheet	1	of	3	Attorney Docket Number	204552035400

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1.	US-6,177,292-B1	01-23-2001	Hong et al.	
	2.	US-6,248,607-B1	06-19-2001	Tsutsui	
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	4.	US-6,475,277-B1	11-05-2002	Hirota et al.	
	5.	US-2002/0192507-A1	12-19-2002	Dwilinski et al.	
	6.	US-6,627,552-B1	09-30-2003	Nishio et al.	
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
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				Examiner Name	F. C. Hiteshew
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	40.	JP-2001-077038	03-23-2001	Sumitomo Electric Industries	Translation of abstract and corresponds to US-6,475,277 listed above	
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NON PATENT LITERATURE DOCUMENTS					
Examine r Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
	50.	Supplementary European Search Report, dated September 23, 2008, European Patent Application No.02788783.5; 3 pages			
	51.	Chinese Office Action, dated July 18, 2008, directed to Chinese Patent Application No. 200580040008.X; 25 pages			✓
	52.	Chinese Office Action, dated December 28, 2007, directed to Chinese Patent Application No. 02802023.5; 8 pages			✓
	53.	Japanese Notification, mailed March 14, 2006, directed to Japanese Patent Application No. 2003-50367; 3 pages			✓
	54.	Japanese Notification of Reason(s) for Refusal, mailed December 16, 2008, directed to Japanese Patent Application No. 2004-505416; 7 pages			✓
	55.	Japanese Notification of Reason(s) for Refusal, mailed January 6, 2009, directed to Japanese Patent Application No. 2004-506101; 7 pages			✓

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72.	Penkala, T., (1972). "Zarys Krystalografii (Basics of Crystallography)". PWN, Warszawa: 349	✓

Examiner Signature	/Felisa Hiteshew/	Date Considered	06/05/2009
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